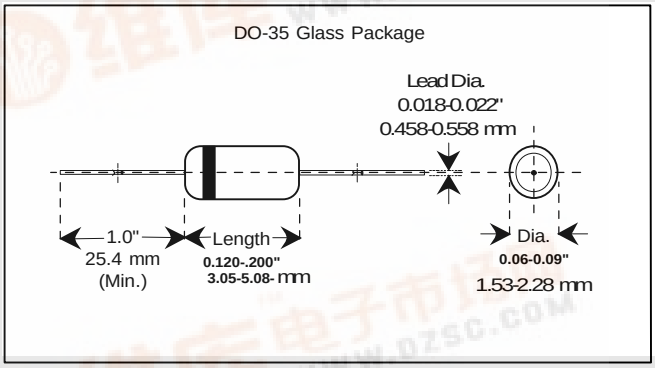
Silicon Switching Diode — 1N4607 — DO-35 Glass Package

Applications

Used in general purpose applications,where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	85 (Min).	Volts
Average Rectified Current	Iavg	200	mAmps
Continuous Forward Current	I_{Fdc}	200	mAmps
Peak Surge Current (t_{peak} = 1 sec.)	I_{peak}	1.0	Amp
BKC Power Dissipation T_L=50 °C, L = 3/8" from body	P_{tot}	500	mWatts
Operating Temperature Range	T_{Op}	-65 to +200	° C
Storage Temperature Range	T_{St}	-65 to +200	° C

Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I_F = 400 mA	V_F	***	1.10	Volts
Breakdown Voltage @ I_R = 25 µA	PIV	85		Volts
Reverse Leakage Current @ V_R = 50 V	I_R		100	µA
Reverse Recovery time (note 1)	t_{rr}		10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA,Vr = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED

Microsemi
6 Lake Street - Lawrence, MA 01841
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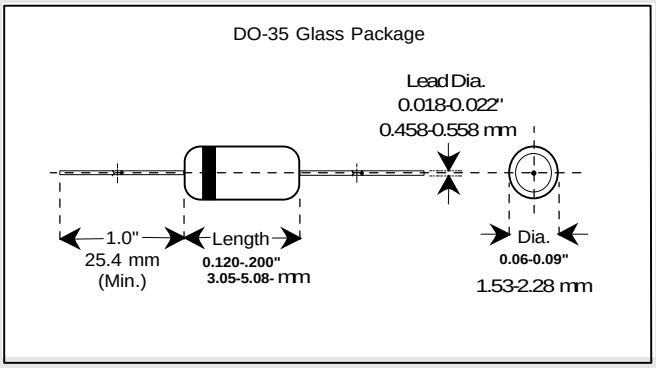

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Average Rectified Current	Iavg	200	mAmps
Continuous Forward Current	I_{Fdc}	500	mAmps
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BKC Power Dissipation T_L=50 °C, L = 3/8" from body	P_{tot}	500	mWatts
Operating Temperature Range	T_{Op}	-65 to +150	° C
Storage Temperature Range	T_{St}	-65 to +150	° C

Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I_F = 400 mA	V_F	***	1.10	Volts
Breakdown Voltage @ I_R = 25 µA	PIV	85		Volts
Reverse Leakage Current @ V_R = 50 V	I_R		100	µA
Reverse Recovery time (note 1)	t_{rr}		10	nSecs

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Silicon Switching Diode  LL-35 Glass Package

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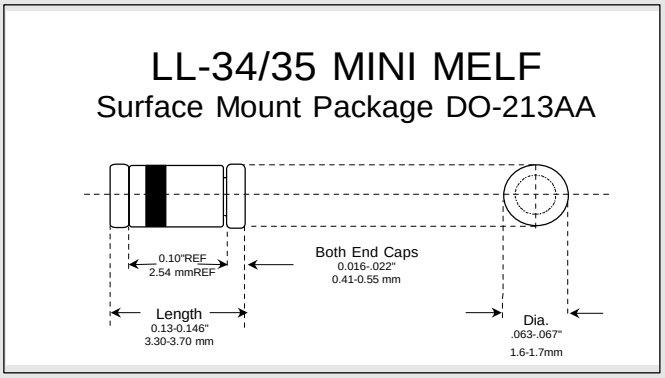

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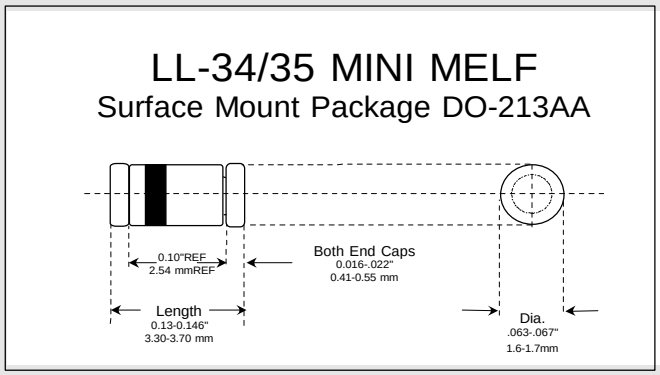

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